

L Number	Hits	Search Text	DB	Time stamp
1	0	5519241.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:30
2	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:31
3	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:32
4	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier same drain\$3) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:33
5	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$2 same drain\$3) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:33
6	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$2 same contact) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:34
7	0	(thyristor same semiconductor) and @ad<20021028 and (emitter) and (doped adj well) and (carrier\$2 same contact) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:35
8	0	(thyristor same semiconductor) and @ad<20021028 and (emitter) and (doped adj well) and (carrier\$2 same (contact or drain\$3)) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:37
9	0	(thyristor same semiconductor) and @ad<20021028 and (emitter) and (doped adj well) and (carrier\$2 same (contact or drain\$3 or well)) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:37
-	70354	thyristor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:21
-	10634	thyristor same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:21
-	7517	(thyristor near8 semiconductor) anmd	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:44
-	2	6756612.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:28
-	6559	(thyristor near8 semiconductor) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:49
-	41	(thyristor near8 semiconductor) and @ad<20021028 and (doped adj emitter)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:50
-	1	(thyristor near8 semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:24
-	2	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:51

	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier asd coupler) and (carrier adj drainage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:53
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier asd coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:53
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:54
	2	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier asd coupler)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/04 10:30
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 15:59
	2	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier asd coupler) and control	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:02
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier and coupler) and control	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:27
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and control	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:07
	0	6756612.ccls. and (thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and control	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:09
	0	6756612.ccls. and (thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:11
	0	6756612.ccls. and (thyristor same semiconductor) and @ad<20021020 and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:12
	0	6756612.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:12
	1	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:12
	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:14
	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021027	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:15
	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021006	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:15

	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021025	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:18
	1	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021030	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:19
	1	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port). and @ad<20021029	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:19
	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:20
	1	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj coupler) and (control adj port) and @ad<20021029	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/18 16:20
	2	6756612.pn. and (carrier adj coupler)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 09:52
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 11:30
	1	(thyristor same semiconductor) and @ad<20021029 and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 11:33
	1	(thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:33
	2	6229161.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 11:55
	2	6104045.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 11:57
	2	4797373.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 11:59
	2	6225165.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:01
	2	5528062.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:02
	0	5528062.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:03
	0	5132767.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:03

	2	5132767.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:03
	2	6084274.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:04
	2	5600160.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:04
	2	6545297.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:05
	0	6545297.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:05
	2	6583452.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:10
	1	6583452.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:30
	0	4395723.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:30
	2	4395723.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:30
	2	20020190265.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:31
	0	20020190265.pn. and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:31
	0	438/268.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:36
	1	257/180,163,156,155,133,.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:38
	1	257/180,163,156,155,133.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:23
	0	438/134,135,136,137,138,139,140.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:57
	4	438/134,135,136,137,138,139,140.ccls. and (thyristor same semiconductor) and (emitter) and (well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:58
	4	438/134,135,136,137,138,139,140.ccls. and (thyristor same semiconductor) and (emitter) and (well) and (control adj port) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 12:59
	4	438/134,135,136,137,138,139,140.ccls. and (thyristor same semiconductor) and (emitter) and (well) and (control adj port) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:33

	2	6756612.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/19 15:49
	2	6777271.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 12:31
	1	6777271.pn. and anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:18
	1	6777271.pn. and anneal\$3 and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:20
	0	6777271.pn. and anneal\$3 and (control adj port) and (carrier adj coupler)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:20
	0	6777271.pn. and anneal\$3 and (control adj port) and (carrier same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:22
	0	6777271.pn. and anneal\$3 and (control adj port) and (carrier\$3 same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:22
	1	6777271.pn. and anneal\$3 and (control adj port) and (contact same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:23
	89714	6777271.pn. (contact same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:25
	1	6777271.pn. and (contact same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:25
	0	6777271.pn. and (contact same drain\$3 and carrier\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:26
	0	6777271.pn. and (contact same drain\$3 same carrier\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:26
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$3 same contact same drain\$3) and control	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:28
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$3 same contact same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:28
	0	438/134, 135, 136, 137, 138, 139, 140.cccls. and (thyristor same semiconductor) and (trench) and (well) and (control adj port) and @ad<20021028 and carrier	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 13:34
	3	438/134, 135, 136, 137, 138, 139, 140.cccls. and (thyristor same semiconductor) and (trench) and (well) and (control adj port) and @ad<20021028	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 14:35
	0	6653174.pn. and (doped adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 14:37
	0	6653174.pn. and ((doped adj well) same carrier\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 14:38

	2	6548905.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/01 15:18
	1	257/180,163,156,155,133,134.ccls. and (thyristor same semiconductor) and (doped adj emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:23
	1	257/180,163,156,155,133,134.ccls. and (thyristor same semiconductor) and (emitter) and (doped adj well) and (control adj port)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:23
	2	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:25
	2	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and carrier\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:49
	0	(thyristor same semiconductor) and @ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$2 same drain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:53
	2	2002113267.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:54
	2	6498372.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:56
	1	1989DE-3908281.PRAI,AP.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 09:59
	1	2001US-0992629.PRAI,AP.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 10:01